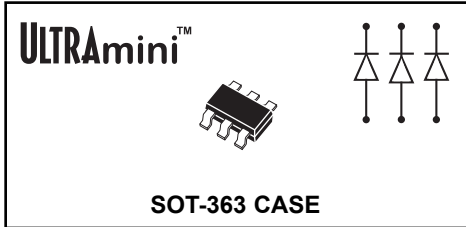


**CMKD6001**  
**SURFACE MOUNT**  
**ULTRAmimi™**  
**TRIPLE ISOLATED**  
**LOW LEAKAGE SILICON**  
**SWITCHING DIODES**



# Central™

## Semiconductor Corp.

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMKD6001 type contains three (3) Isolated Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a ULTRAmimi™ surface mount package, designed for switching applications requiring extremely low leakage.

**MARKING CODE: K01**

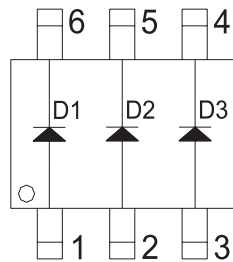
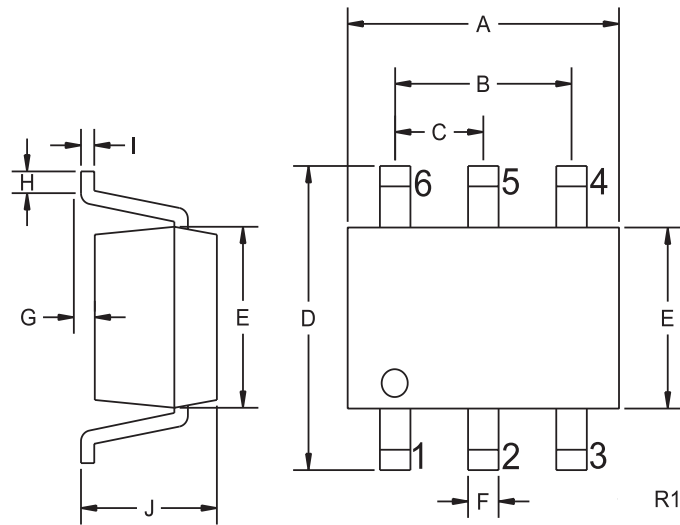
**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	<b>SYMBOL</b>		<b>UNITS</b>
Continuous Reverse Voltage	$V_R$	75	V
Peak Repetitive Reverse Voltage	$V_{RRM}$	100	V
Continuous Forward Current	$I_F$	250	mA
Peak Repetitive Forward Current	$I_{FRM}$	250	mA
Forward Surge Current, $t_p=1 \mu\text{sec.}$	$I_{FSM}$	4000	mA
Forward Surge Current, $t_p=1 \text{ sec.}$	$I_{FSM}$	1000	mA
Power Dissipation	$P_D$	250	mW
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\Theta_{JA}$	500	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER DIODE:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNITS</b>
$I_R$	$V_R=75\text{V}$		500	pA
$BV_R$	$I_R=100\mu\text{A}$	100		V
$V_F$	$I_F=1.0\text{mA}$		0.85	V
$V_F$	$I_F=10\text{mA}$		0.95	V
$V_F$	$I_F=100\text{mA}$		1.1	V
$C_T$	$V_R=0, f=1 \text{ MHz}$		2.0	pF
$t_{rr}$	$I_R=I_F=10\text{mA}, R_L=100\Omega \text{ Rec. to } 1.0\text{mA}$		3.0	$\mu\text{s}$

**SOT-363 CASE - MECHANICAL OUTLINE**



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.073	0.085	1.85	2.15
B	0.051		1.30	
C	0.026		0.65	
D	0.075	0.091	1.90	2.30
E	0.043	0.055	1.10	1.40
F	0.006	0.012	0.15	0.30
G	0.000	0.004	0.00	0.10
H	0.010	-	0.25	-
I	0.004	0.010	0.10	0.25
J	0.031	0.039	0.80	1.00

SOT-363 (REV: R1)

**LEAD CODE:**

- 1) ANODE 1
- 2) ANODE 2
- 3) ANODE 3
- 4) CATHODE 3
- 5) CATHODE 2
- 6) CATHODE 1

**MARKING CODE: K01**

R1 (13-November 2002)